

IN THE TITLE:

Please amend the Title to read:

"SEMICONDUCTOR DEVICE COMPRISING A HIGHLY-RELIABLE,
CONSTANT CAPACITANCE CAPACITOR".

IN THE ABSTRACT:

Please amend the Abstract as follows. A clean copy of the Abstract on a separate sheet of paper is appended hereto.

[Obtained are a semiconductor device which can be implemented with high density of integration while ensuring a constant capacitor capacitance in high reliability and a method of fabricating the same. The] A semiconductor device, including a memory cell region and a peripheral circuit region, comprises an insulating film, having an upper surface, formed on a major surface of a semiconductor substrate to extend from the memory cell region to the peripheral circuit region. A capacitor lower electrode assembly is formed in the memory cell region to upwardly extend [beyond] to substantially the same height as the upper surface of the insulating film on the major surface of the semiconductor substrate. Additionally, the lower electrode assembly includes first and second lower electrodes that are adjacent through the insulating film. A capacitor upper electrode is formed on the capacitor lower electrode through a dielectric film, to extend onto the upper surface of the insulating film. The capacitor lower electrode includes a capacitor lower electrode part having a top surface and a bottom surface. [The upper surface of the insulating film is located between the top surface and the bottom surface of the capacitor lower electrode part] A semiconductor device